

20V P-Channel Enhancement Mode MOSFET

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Product Summary

- $V_{DS} = -20V, I_{D} = -6A$
 - $R_{DS(ON)}$ < 28m Ω (max) @ V_{GS} =-2.5V
 - $R_{DS(ON)}$ < 20m Ω (max) @ V_{GS}=-4.5V

Application

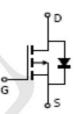
- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

Package and Pin Configuration

SOT-23



Circuit diagram



Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	-20	V
Gate-Source Voltage	Vgs	±12	V
Drain Current -Continuous	I _D	-6	А
Drain Current -Pulsed (Note 1)	I _{DM}	-24	Α
Maximum Power Dissipation	P _D	1.8	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	R _{0JA}	69	°C/W
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Off Characteristics	MI.	20			×		
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-20	-	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-12V,V _{GS} =0V	2.7	-	-1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±12V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)	1.						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250μA	-0.4	-0.55	-1.0	V	
Danie Course On Otata Basistana	Б	V _{GS} =-4.5V, I _D =-6A	(-/	18	20	0	
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =-2.5V, I _D =-5A), \	22	28	mΩ	
Forward Transconductance	g _{FS}	V _{DS} =-5V,I _D =-6A		20	-	S	
Dynamic Characteristics (Note4)							
Input Capacitance	C _{lss}	V - 0VV -0V	-	1730	-	PF	
Output Capacitance	C _{oss}	V _{DS} =-6V,V _{GS} =0V, F=1.0MHz - 320 210 -	-	320		PF	
Reverse Transfer Capacitance	C _{rss}		PF				
Switching Characteristics (Note 4)		VX		No	e.	***	
Turn-on Delay Time	t _{d(on)}	7/1/	-	20		nS	
Turn-on Rise Time	tr	V_{DD} =-6 V , I_D =-1 A ,	-	35	-	nS	
Turn-Off Delay Time	$t_{d(off)}$	$R_L=6\Omega, V_{GEN}=-4.5V, R_g=6\Omega$	-	90	-	nS	
Turn-Off Fall Time	t _f	/ X /	_	70	-	nS	
Total Gate Charge	Qg		-	19.5		nC	
Gate-Source Charge	Q _{gs}	V _{DS} =-6V,I _D =-6A,V _{GS} =-4.5V	_	4.1	-	nC	
Gate-Drain Charge	Q_{gd}		-	5.2	-	nC	
Drain-Source Diode Characteristics							
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1.0A	-	-	-1.2	V	
Diode Forward Current (Note 2)	Is		-	-	-6	А	



Typical Electrical and Thermal Characteristics

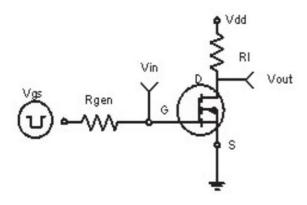


Figure 1:Switching Test Circuit

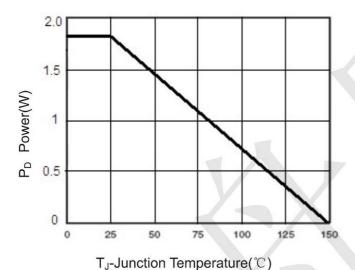


Figure 3 Power Dissipation

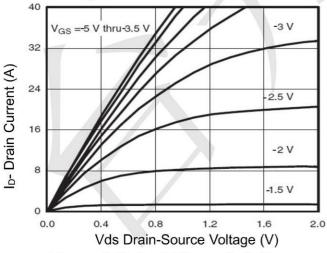


Figure 5 Output Characteristics

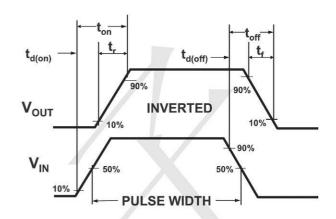
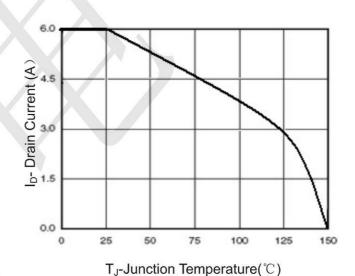


Figure 2:Switching Waveforms



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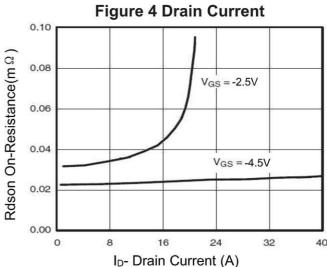


Figure 6 Drain-Source On-Resistance



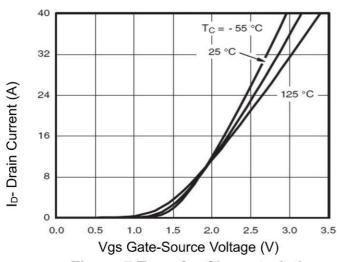


Figure 7 Transfer Characteristics

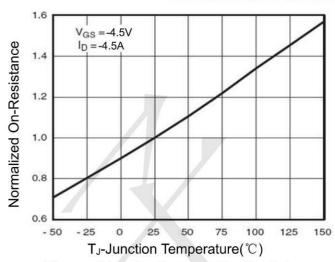


Figure 8 Drain-Source On-Resistance

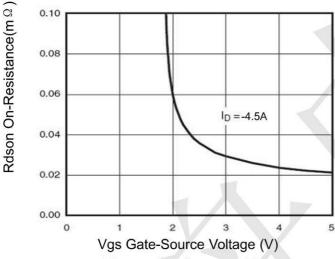


Figure 9 Rdson vs Vgs

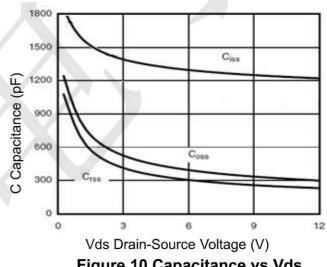
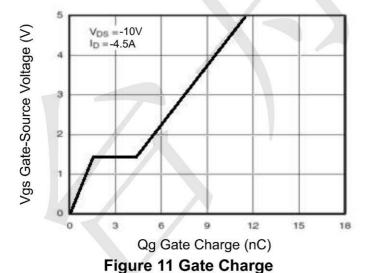


Figure 10 Capacitance vs Vds



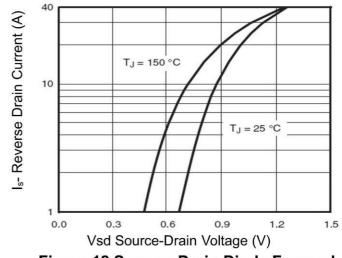


Figure 12 Source- Drain Diode Forward



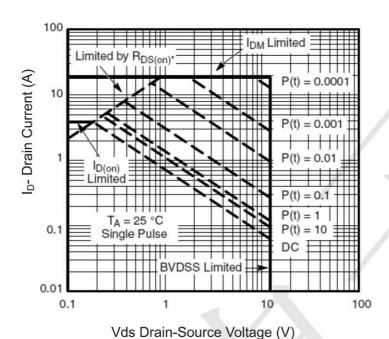


Figure 13 Safe Operation Area

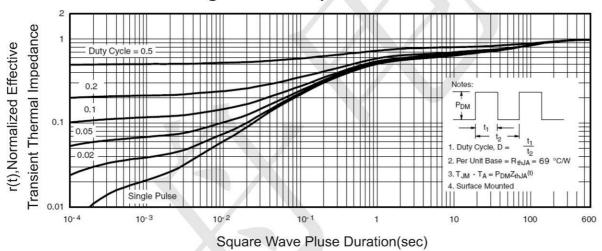
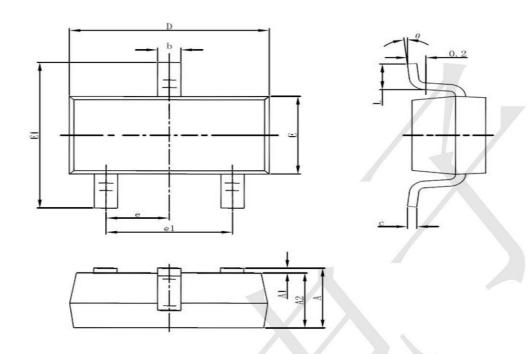


Figure 14 Normalized Maximum Transient Thermal Impedance



3-pin SOT23-3 Outline Dimensions



Symbol	Dimensions In	Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
Α	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
С	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
е	0.950(BSC)		0.037(1	BSC)
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

